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C3 Semiconductor, LLC

POWER COMPONENTS

**Applications**

- Phase Control
- Static Switching
- Light Dimming
- Motor Speed Control
- Kitchen Equipment
- Power Tools
- Solenoid Valve Controls:
  - Dishwashers
  - Washing Machines

- > **Suitable for General Purpose AC Switching**
- > **400A Surge**
- > **IGT = 50 mA**
- > **V<sub>DRM</sub>/V<sub>RMM</sub> 400, 600, 800V**

**CTA/CTB41**40Amp - 400/600/800V - **TRIAC****Absolute Maximum Ratings**

	CONDITIONS	SYMBOL	RATING
RMS On-State Current (full sine wave)	T <sub>c</sub> = 80°C T <sub>c</sub> = 95°C	TO-218 TO-218 Iso	I <sub>T(RMS)</sub> 40A
Non Repetitive Surge Peak On-State Current (Full Cycle, T <sub>j</sub> Initial = 25°C)	F = 50 Hz F = 60 Hz	I <sub>TSM</sub>	400A 420A
I <sup>2</sup> t Value for fusing	tp = 10 ms	I <sup>2</sup> t	880A <sup>2</sup> s
Critical rate of rise of on-state current I <sub>G</sub> = 2 x I <sub>GT</sub> , tr < 100 ns, T <sub>j</sub> = 125°C		di/dt	100A/μs
Peak Gate Current @ T <sub>j</sub> = 125°C	tp = 20 μs	I <sub>GM</sub>	4A
Average Gate Power Dissipation @ T <sub>j</sub> = 125°C		P <sub>G(AV)</sub>	1W
Storage Temperature Range		T <sub>stg</sub>	-40 to +150°C
Operating Junction Temperature Range		T <sub>j</sub>	-40 to +125°C
Isolation Voltage (CTA Series only)		V <sub>ISO</sub>	2500 V <sub>RMS</sub>

**Electrical Characteristics****ALTERNISTOR/NO SNUBBER AND LOGIC LEVEL (3 Quadrants)**

		BW
I <sub>GT</sub> MAX @ V <sub>D</sub> = 12 V, R <sub>L</sub> = 30Ω <sup>NOTE 1</sup>	QI-II-III	50mA
V <sub>GT</sub> MAX @ V <sub>D</sub> = 12 V, R <sub>L</sub> = 30Ω	QI-II-III	1.3V
V <sub>GD</sub> MIN @ V <sub>D</sub> = V <sub>DRM</sub> , R <sub>L</sub> = 3.3kΩ	QI-II-III	0.2V
I <sub>H</sub> MAX @ I <sub>T</sub> = 500 mA <sup>NOTE 2</sup>		75mA
I <sub>L</sub> MAX @ I <sub>G</sub> = 1.2 I <sub>GT</sub>	QI-III	70mA
I <sub>L</sub> MAX @ I <sub>G</sub> = 1.2 I <sub>GT</sub>	Q-II	100mA
dv/dt MIN @ V <sub>D</sub> = 67%V <sub>DRM</sub> (gate open) <sup>NOTE 2</sup>	T <sub>j</sub> = 125°C	1000V/μs
(di/dt) <sub>c</sub> MIN without Snubber <sup>NOTE 2 &amp; 4</sup>	T <sub>j</sub> = 125°C	22A/ms

**STANDARD (4 Quadrants)**

		B
I <sub>GT</sub> MAX @ V <sub>D</sub> = 12 V, R <sub>L</sub> = 30Ω <sup>NOTE 1</sup>	QI-II-III	50mA
I <sub>GT</sub> MAX @ V <sub>D</sub> = 12 V, R <sub>L</sub> = 30Ω <sup>NOTE 1</sup>	QIV	100mA
V <sub>GT</sub> MAX @ V <sub>D</sub> = 12 V, R <sub>L</sub> = 30Ω	Q-All	1.3V
V <sub>GD</sub> MIN @ V <sub>D</sub> = V <sub>DRM</sub> , R <sub>L</sub> = 3.3kΩ	Q-All	0.2V
I <sub>H</sub> MAX @ I <sub>T</sub> = 100 mA <sup>NOTE 2</sup>		75mA
I <sub>L</sub> MAX @ I <sub>G</sub> = 1.2 I <sub>GT</sub>	QI-III-IV	75mA
I <sub>L</sub> MAX @ I <sub>G</sub> = 1.2 I <sub>GT</sub>	Q-II	160mA
dv/dt MIN @ V <sub>D</sub> = 67%V <sub>DRM</sub> (gate open) <sup>NOTE 2</sup>	T <sub>j</sub> = 125°C	500V/μs
(dv/dt) <sub>c</sub> MIN @ (di/dt) <sub>c</sub> = 13.3 A/ms <sup>NOTE 2</sup>	T <sub>j</sub> = 125°C	10V/μs



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**GENERAL NOTES**

1. Minimum IGT is guaranteed at 5% of IGT max.
2. For both polarities of A2 referenced to A1
3. All parameters at 25 degrees C unless otherwise specified.
4. Commutating dv/dt = 50V/μs, (exponential to 200 Vpk)

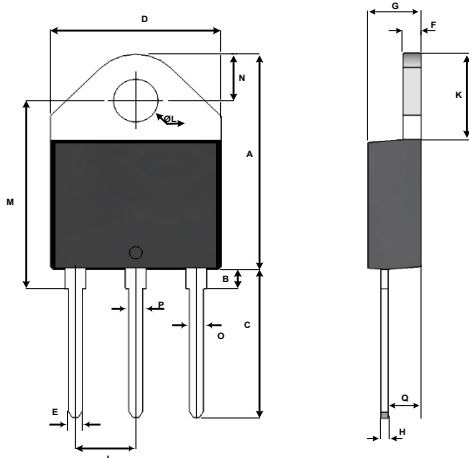


## Static Characteristics

$V_T$ MAX @ $I_{TM} = 35$ A, $t_p = 380\mu s$ NOTE 2	$T_j = 25^\circ C$	1.55V
$V_{TO}$ MAX @ Threshold Voltage NOTE 2	$T_j = 125^\circ C$	0.85V
$R_d$ MAX @ Dynamic Resistance NOTE 2	$T_j = 125^\circ C$	16m $\Omega$
$I_{DRM}$ MAX @ $V_{DRM} = V_{RRM}$	$T_j = 25^\circ C$	5 $\mu$ A
$I_{RRM}$ MAX @ $V_{DRM} = V_{RRM}$	$T_j = 125^\circ C$	3mA

## Thermal Resistances

		SYMBOL	RATING
Junction to Case (AC)	TO-218	Rth(j-c)	0.8°C/W
Junction to Case (AC)	TO-218 Isolated	Rth(j-c)	1.1°C/W
Junction to Ambient	TO-218	Rth(j-a)	50°C/W
Junction to Ambient	TO-218 Isolated	Rth(j-a)	50°C/W



## Dimensions

REF.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	20.4		21.1	0.8		0.831
B		3.23			0.127	
C	14.35		15.60	0.565		0.614
D	15.1		15.5	0.594		0.610
E	1.20		1.40	0.047		0.055
F	1.45		1.55	0.057		0.061
G	4.4		4.6	0.173		0.181
H	0.5		0.7	0.020		0.028
J	5.4		5.65	0.213		0.222
K	8.0		8.25	0.315		0.325
L	4.08		4.17	0.161		0.164
M	15.8		16.5	0.622		0.650
N	4.6		4.8	0.181		0.189
O	1.20		1.40	0.047		0.055
P	1.20		1.40	0.047		0.055
Q	2.7		2.9	0.106		0.114

## Part Number Selection

Part Number	Voltage [Vpk]	$I_{GT}$ [mA]	Type	Package
CTA/CTB41-xxxB	400, 600, 800	50mA	Standard	TO-218
CTA/CTB41-xxxBW	400, 600, 800	50mA	Alternistor/No Snubber	TO-218

## Part Number Designation

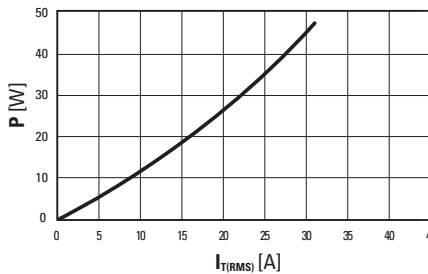
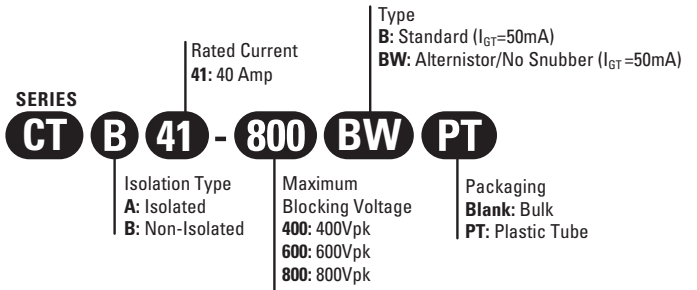


Fig. 1: Power dissipation versus RMS on-state current (full cycle).

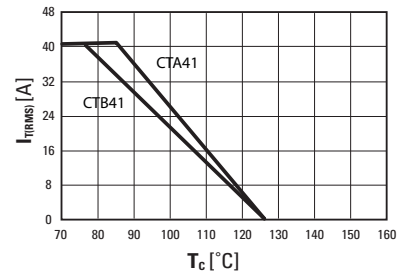


Fig. 2: RMS on-state current versus case temperature (full cycle)

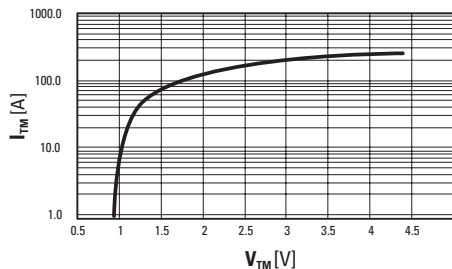


Fig. 3: On-state current versus on-state voltage (instantaneous values)

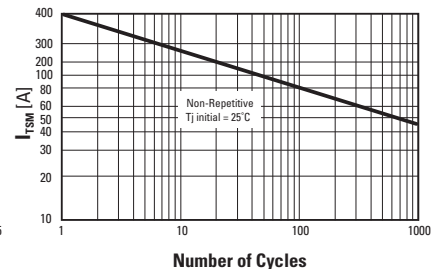


Fig. 4: Non-repetitive surge peak on-state current versus number of cycles.

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Approvals

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